Poster Presentation

[AMDp1]Oxide TFTs

Thu. Nov 28, 2019 10:40 AM - 1:10 PM Main Hall (1F)

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[AMDp1-14]Effect of Mo and MoTi Serving as a Barrier Layer for Cu Source/Drain Electrodes on Performances of Amorphous Silicon and IGZO TFTs

*Chuanbao Luo[1], Qianyi Zhang[1], Ziran Li[1], Xuechao Ren[1], Xiaolong Meng[1], Dai Tian[1], Bisheng Mo[1], Xiaohu Wei[1], Xialiang Yuan[1], Shijian Qin[1] (1. Shenzhen China Star Optoelectronics Technology Co., Ltd (China))

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The research reveals the effect of Mo and MoTi film on the suppression of Cu diffusion for BCE structure of a-Si and a-IGZO devices during severe thermal process. Electrical characters depict that a-IGZO film is superior to a-Si for suppressing Cu diffusion, resulting from untraceable Cu signal in ToF-SIMS.